## Letter

# Phase study of the system Cu<sub>1-x</sub>Li<sub>x</sub>InSe<sub>2</sub>

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Both constituent compounds of the alloy system under investigation belong to the large family of ternary chalcogenides that form lattices with tetrahedral coordination of the atoms. At ambient conditions CuInSe<sub>2</sub> crystallizes in the chalcopyrite structure which is a superstructure of the sphalerite lattice; undergoes with heating a polymorphous phase transition from the chalcopyrite to the sphalerite structure at 810 °C; and melts congruently at 986 °C [1]. Structure and differential thermoanalysis (DTA) studies of LiInSe<sub>2</sub> [2, 3] have shown that this compound crystallizes in the orthorhombic β-NaFeO<sub>2</sub> structure which represents a distorted superstructure of the wurtzite lattice. The melting temperature is 904 °C, and in contrast to CuInSe<sub>2</sub> no phase transitions of solid LiInSe<sub>2</sub> were observed between room temperature and the melting point. It was the aim of the present work to study the phase diagram of the quasi-binary alloy system Cu<sub>1-x</sub>Li<sub>x</sub>InSe<sub>2</sub> in order

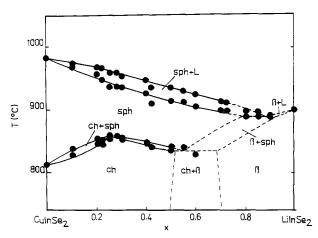


Fig. 1. Phase diagram of the system  $Cu_{1-x}Li_xInSe_2$  (L-liquid, sph-sphalerite, ch-chalcopyrite,  $\beta$ - $\beta$ -NaFeO<sub>2</sub> structure).

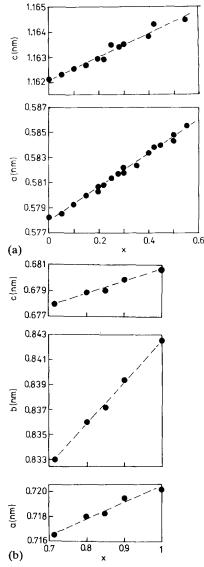


Fig. 2. Lattice parameters at room temperature of  $Cu_{1-x}Li_xInSe_2$  alloys in the composition ranges with (a) chalcopyrite structure and (b)  $\beta$ -NaFeO<sub>2</sub> structure.

to define the region of solubility; to establish the stability ranges of the closely related but different structures of the alloy constituents; and to look for other ordered phases as they have been found, for instance, in some alloys of ternary chalcopyrite-structure chalcogenides with binary wurtzite or sphalerite-structure chalcogenides [4–6].

Alloy samples of the desired compositions were prepared by solid state reaction of corresponding mixtures of the constituent compounds. The constituent compounds themselves were synthesized by vacuum fusion L18 Letter

of stoichiometric amounts of the high-purity elements (99.99% Li, 99.999% Cu, 99.9999% In and Se) using standard procedures as they have been described elsewhere for both CuInSe<sub>2</sub> [7, 8] and LiInSe<sub>2</sub> [2, 9]. These ternary starting materials were crushed to powder, taken in the desired proportions, thoroughly mixed for homogenization and sealed in quartz ampoules evacuated to a residual gas pressure of  $10^{-2}$ – $10^{-3}$  Pa. The charges were then annealed at 650, 780 and 800 °C for 72 days and at 900 °C for 30 days and afterwards quenched to liquid nitrogen or room temperature. For each of the annealing regimes a complete set of samples for the whole composition range was prepared in order to control the state of the reaction process. We found that annealing at 650 °C for 72 days and equally well annealing at 900 °C for 30 days ensures complete reaction of the constituents to a homogeneous alloy.

DTA measurements were made by means of a Setaram microthermoanalyser in the temperature range T=300-1050 °C ( $\Delta T=\pm 5$  K) at a heating rate of 3 K min<sup>-1</sup>. In constructing the phase diagram we followed the same procedure as described in ref. 6. X-ray powder diffraction using filtered CuK<sub>\alpha</sub> radiation and silicon as the internal standard was used to identify the structure and to determine the lattice parameters of the samples, in all cases with an accuracy of  $\pm 0.0004$  nm or better.

The resulting phase diagram of the system Cu<sub>1-x</sub>Li<sub>x</sub>InSe<sub>2</sub> is shown in Fig. 1. At temperatures below 800 °C including room temperature the samples always have the chalcopyrite structure in the mole fraction range  $0 \le x \le 0.5$  and the orthorhombic  $\beta$ -NaFeO<sub>2</sub> structure for  $0.7 \le x \le 1.0$ . At mole fractions of 0.5 < x < 0.7reflections from both phases could be identified in the diffraction diagrams. Obviously, this result indicates the presence of a miscibility gap in this composition range of the alloys. Finally, in none of the samples were any traces of an admixture of a sphalerite phase found at temperatures below about 800 °C. Consequently, it can be argued that alloy formation results in a random distribution of Cu and Li atoms on sites of the Group I cation sublattice on both the CuInSe<sub>2</sub> and LiInSe<sub>2</sub>rich sides of the system, while the indium sublattice remains unaffected.

The presence of a polymorphous phase transition was detected in all samples having compositions in the

range  $0 \le x \le 0.6$  (Fig. 1). It is interesting to note that at a mole fraction close to x = 0.25 the phase transition temperature goes through a maximum which, in principle, could give rise to an ordered phase with the formula Cu<sub>3</sub>LiIn<sub>4</sub>Se<sub>8</sub>. However, even very careful examination of the X-ray diffraction diagrams recorded on samples of this composition range did not give any hints to the presence of an additional ordered phase. At compositions x > 0.6 the DTA curves did not show any thermal response due to a polymorphous phase transition. Finally, it follows from Fig. 1 that the melting temperature decreases continuously with increasing Li content of the alloys, from 986 °C for CuInSe<sub>2</sub> to 904 °C for LiInSe<sub>2</sub> with, maybe, a weakly pronounced minimum in the melting temperature curve at a composition close to x = 0.9.

The lattice parameters measured at room temperature are depicted in Fig. 2. In both the chalcopyrite and  $\beta$ -NaFeO<sub>2</sub> structure ranges the lattice parameters increase with increasing Li content of the alloys and all the lattice parameters change with composition according to Vegards rule.

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